

### NCE N-Channel Enhancement Mode Power MOSFET

### **Description**

The NCE0130A uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

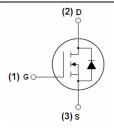
- V<sub>DS</sub> = 100V,I<sub>D</sub> =30A
  - $R_{DS(ON)} < 32m\Omega$  @  $V_{GS}=10V$  (Typ:25m $\Omega$ )
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation

#### **Application**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% AVds TESTED!



#### Schematic diagram



#### Marking and pin assignment



TO-220-3L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0130A	NCE0130A	TO-220-3L	-	-	-

### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Par	ameter	Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	100	V
Gate-Source Voltage		V <sub>G</sub> s	±20	V
Drain Current-Continuou	s	I <sub>D</sub>	30	Α
Drain Current-Continuou	s(TC=100°C)	I <sub>D</sub> (100℃)	21	Α
Pulsed Drain Current (Not	e 1)	I <sub>DM</sub>	120	
Maximum Power Dissipa	ition	P <sub>D</sub>	85	W
Derating factor		0.57		W/°C
Single pulse avalanche	energy <sup>(Note 5)</sup>	E <sub>AS</sub>	200	mJ
V <sub>DS</sub> Spike (Note 6)	10µs	120	V	
Operating Junction and	Storage Temperature Range	$T_J, T_STG$	-55 To 175	$^{\circ}\!\mathbb{C}$

### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)	R <sub>0</sub> JC	1.8	°C/W
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# Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Sym	· · · · · · · · · · · · · · · · · · ·	Parameter	Condition	Min	Тур	Max	Unit
Off Characteristics		_		•			
BV <sub>DSS</sub>	Drain-Source Break	down Voltage	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100	115	-	V
I <sub>DSS</sub>	Zero Gate Voltage	Drain Current	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μA
I <sub>GSS</sub>	Gate-Body Leak	age Current	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)							
V <sub>GS(th)</sub>	Gate Threshol	d Voltage	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	1.3	1.9	2.5	V
R <sub>DS(ON)</sub>	Drain-Source On-St	ate Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	25	32	mΩ
<b>g</b> <sub>FS</sub>	Forward Transco	onductance	V <sub>DS</sub> =5V,I <sub>D</sub> =10A	-	15	-	S
Dynamic Characteris	tics (Note4)			•			
C <sub>lss</sub>	Input Capac	citance		-	2479	-	PF
C <sub>oss</sub>	Output Capa	ıcitance	$V_{DS}$ =50V, $V_{GS}$ =0V, F=1.0MHz	-	96	-	PF
C <sub>rss</sub>	Reverse Transfer	Capacitance	F=1.UIVIHZ	-	79	-	PF
Switching Characteri	stics (Note 4)			•			
t <sub>d(on)</sub>	Turn-on Dela	ay Time		-	9	-	nS
t <sub>r</sub>	Turn-on Ris	e Time	$V_{DD}$ =50V, $R_L$ =5 $\Omega$	-	9	-	nS
t <sub>d(off)</sub>	Turn-Off Dela	ay Time	$V_{GS}$ =10 $V$ , $R_{GEN}$ =3 $\Omega$	-	32	-	nS
t <sub>f</sub>	Turn-Off Fa	II Time		-	8	-	nS
Qg	Total Gate (	Charge	\/ -50\/   -404	-	67.2	-	nC
Q <sub>gs</sub>	Gate-Source	Charge	$V_{DS}=50V,I_{D}=10A,$ $V_{GS}=10V$	-	9.4	-	nC
$Q_{gd}$	Gate-Drain	Charge	V <sub>GS</sub> =10V	-	15.5	-	nC
Drain-Source Diode (	Characteristics			•			
V <sub>SD</sub>	Diode Forward V	oltage (Note 3)	V <sub>GS</sub> =0V,I <sub>S</sub> =10A	-	-	1.2	V
Is	Diode Forward C		-	-	-	30	Α
t <sub>rr</sub>	Reverse Recov	ery Time	TJ = 25°C, IF = 10A	-	32	-	nS
Qrr	Reverse Recove	ery Charge	di/dt = 100A/µs <sup>(Note3)</sup>	-	53	-	nC
t <sub>on</sub>	Forward Turn-	On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+L				y LS+LD)

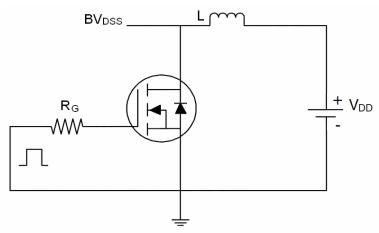
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS Condition : Tj=25  $^{\circ}\text{C}$  ,V  $_{DD}$  =50 V ,V  $_{G}$  =10 V ,L=0.5 mH ,Rg=25  $\Omega$
- 6. The spike duty cycle 5% max, limited by junction temperature  $T_{J}(MAX) \!\!=\! 125^{\circ}\,$  C

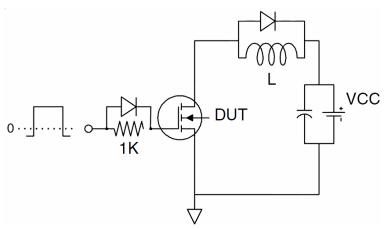


### **Test Circuit**

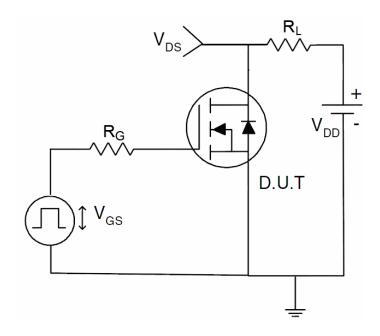
# 1) E<sub>AS</sub> Test Circuit



## 2) Gate Charge Test Circuit

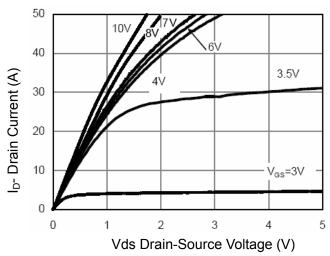


### 3) Switch Time Test Circuit

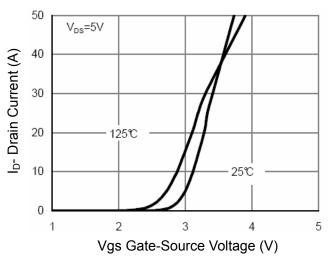




### **Typical Electrical and Thermal Characteristics (Curves)**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

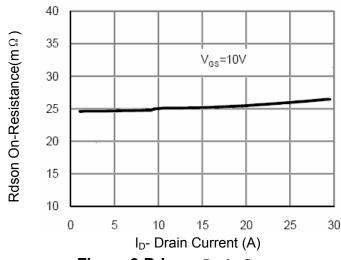


Figure 3 Rdson- Drain Current

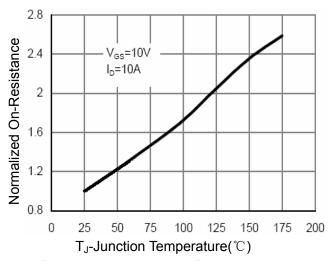


Figure 4 Rdson-JunctionTemperature

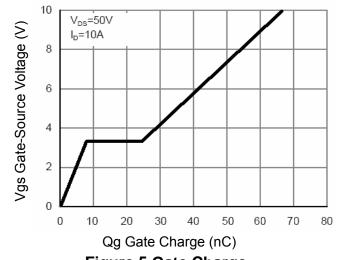


Figure 5 Gate Charge

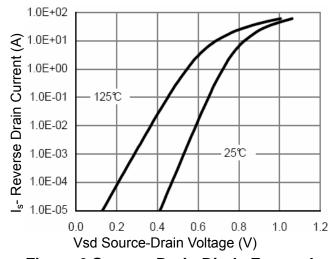
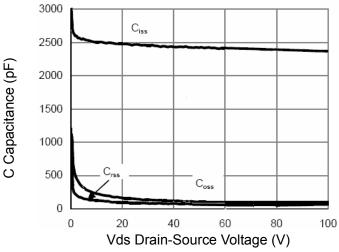


Figure 6 Source- Drain Diode Forward

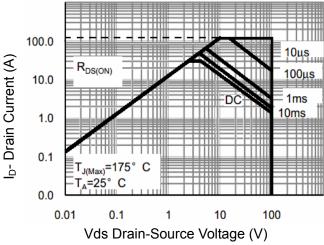


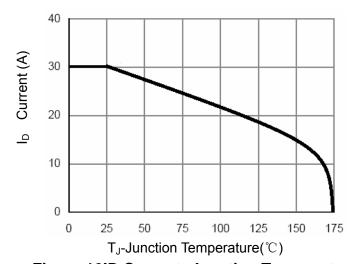


120 100 Power Dissipation (W) 80 60 40 20 0 0 25 50 75 125 100 150 175 T<sub>J</sub>-Junction Temperature (°C)

Figure 7 Capacitance vs Vds

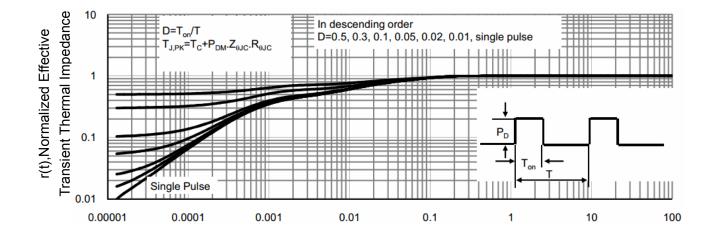
Figure 9 Power De-rating





**Figure 8 Safe Operation Area** 

**Figure 10ID Current- Junction Temperature** 

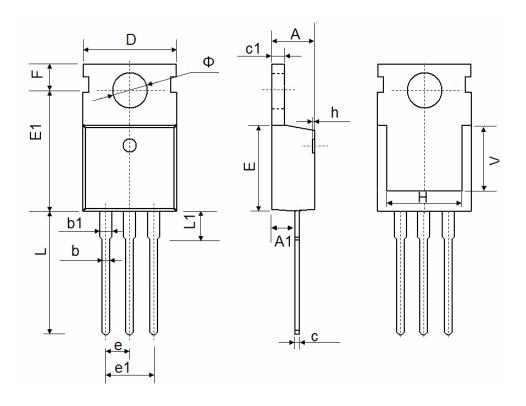


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



# **TO-220-3L Package Information**



Symbol	Dimensions	s In Millimeters	Dimensions In Inches			
	Min.	Max.	Min.	Max.		
A	4.400	4.600	0.173	0.181		
A1	2.250	2.550	0.089	0.100		
b	0.710	0.910	0.028	0.036		
b1	1.170	1.370	0.046	0.054		
С	0.330	0.650	0.013	0.026		
c1	1.200	1.400	0.047	0.055		
D	9.910	10.250	0.390	0.404		
E	8.9500	9.750	0.352	0.384		
E1	12.650	12.950	0.498	0.510		
е	2.54	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204		
F	2.650	2.950	0.104	0.116		
Н	7.900	8.100	0.311	0.319		
h	0.000	0.300	0.000	0.012		
L	12.900	13.400	0.508	0.528		
L1	2.850	3.250	0.112	0.128		
V	7.500 REF.		0.295 REF.			
Ф	3.400	3.800	0.134	0.150		



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